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Chou et al.

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(54) **METHOD AND SYSTEMS FOR AMPLIFYING AN OUTPUT OF A CMOS PIXEL ARRAY**

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H04N 5/00 (2011.01)
H04N 5/378 (2011.01)
H04N 5/365 (2011.01)

(52) **U.S. Cl.**

CPC **H04N 5/378** (2013.01); **H04N 5/3651** (2013.01)

(58) **Field of Classification Search**

CPC ... H04N 5/378; H04N 5/3559; H04N 5/3594; H04N 5/3598
See application file for complete search history.

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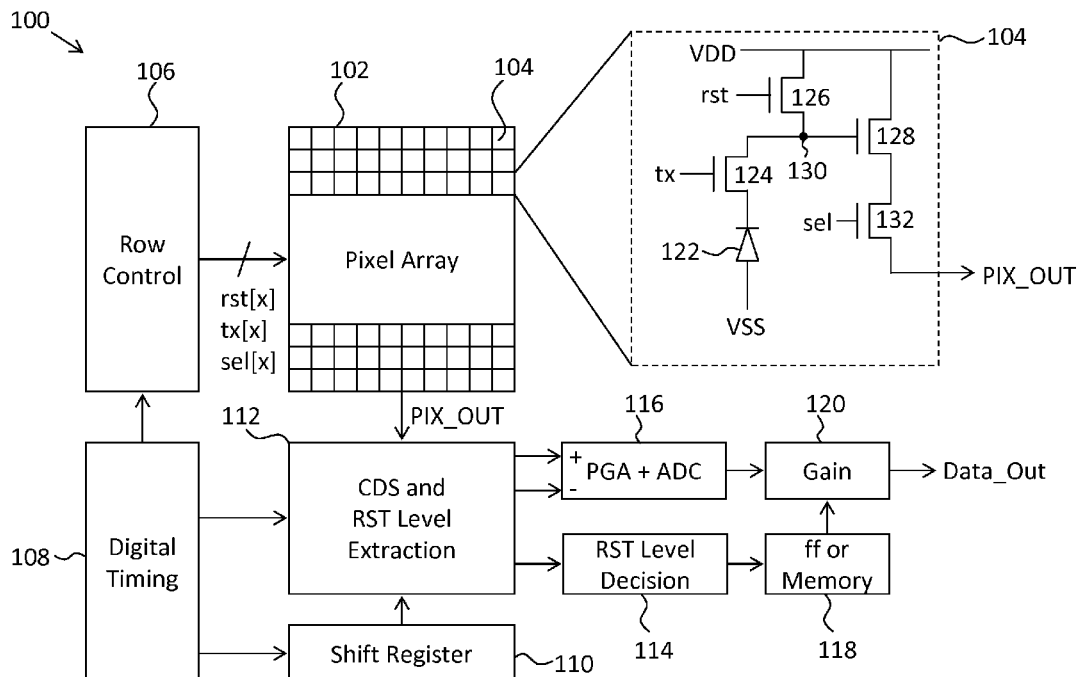
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(57) **ABSTRACT**

A CMOS sensor includes a pixel configured to output a voltage based on incident light received by the pixel. Circuitry is coupled to the pixel and is configured to determine a reset voltage of the pixel and to select a gain level based on the reset voltage of the pixel. A gain circuit is coupled to the circuitry and is configured to set a voltage level of the gain selected by the circuitry.

20 Claims, 8 Drawing Sheets



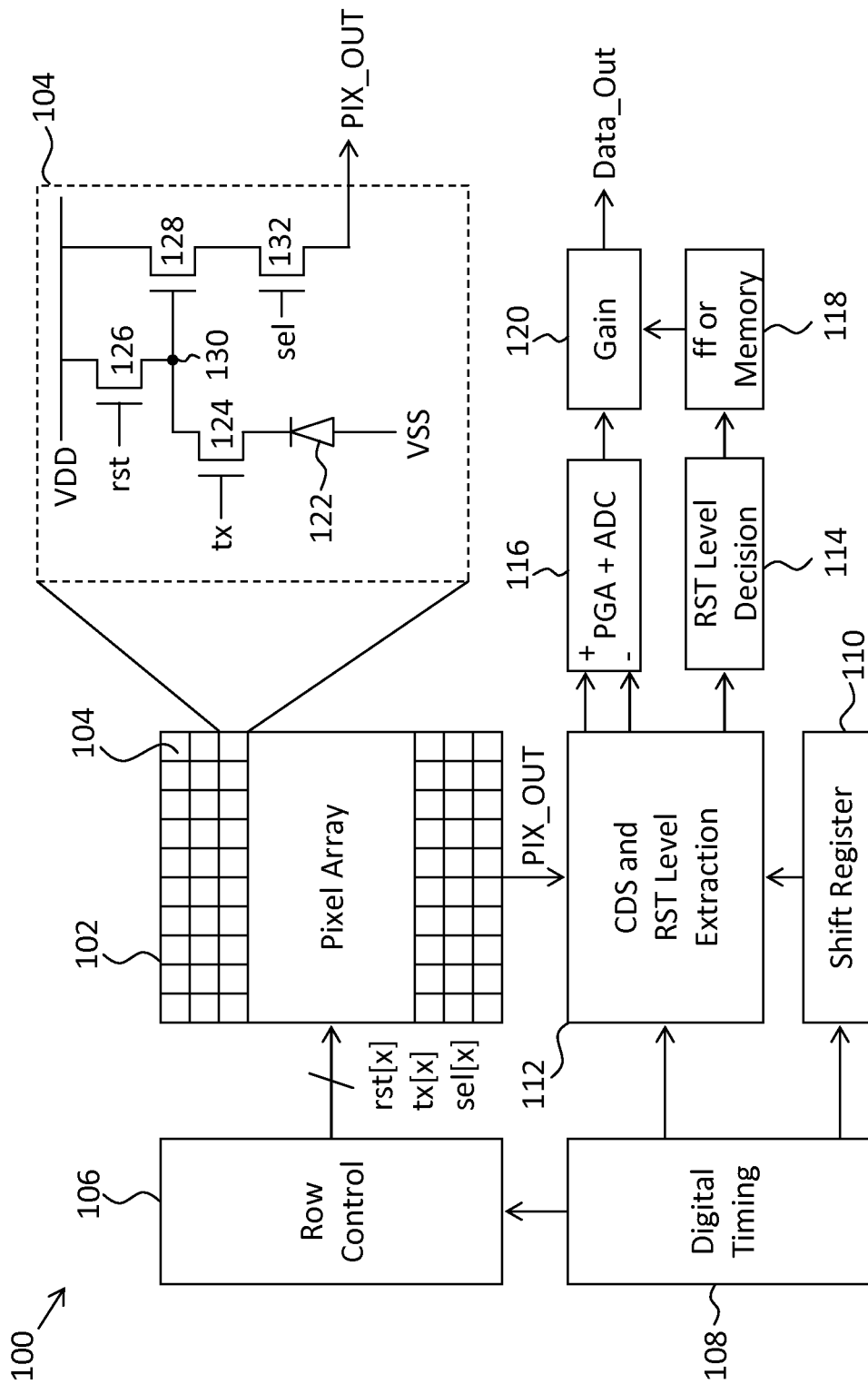


FIG. 1

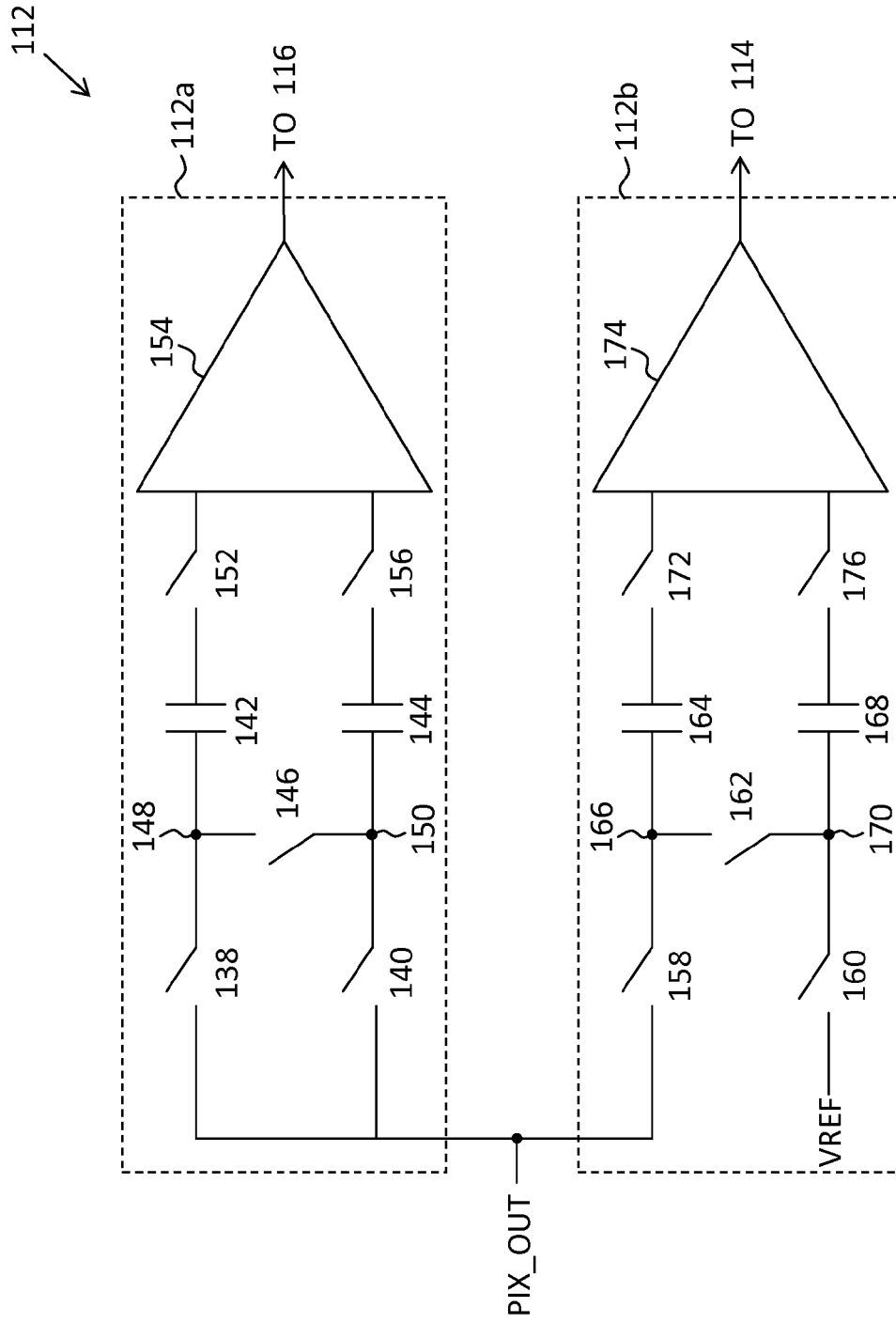


FIG. 2

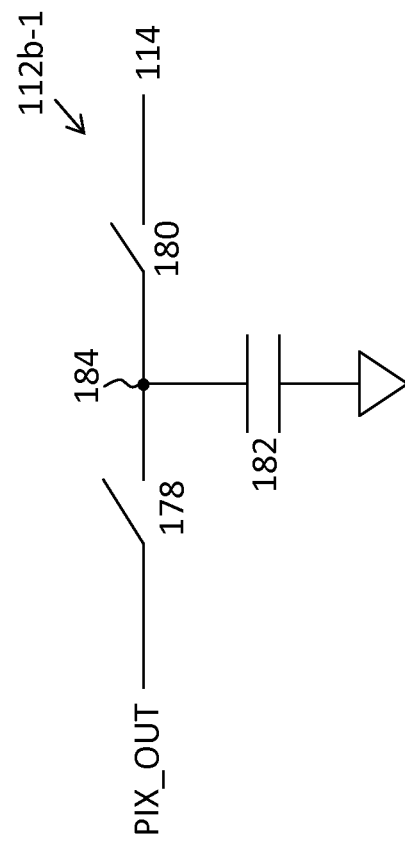


FIG. 3A

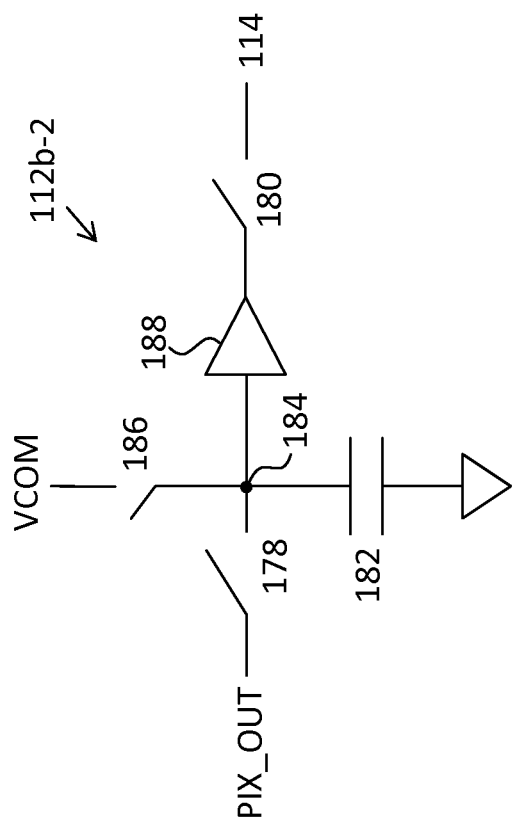


FIG. 3B

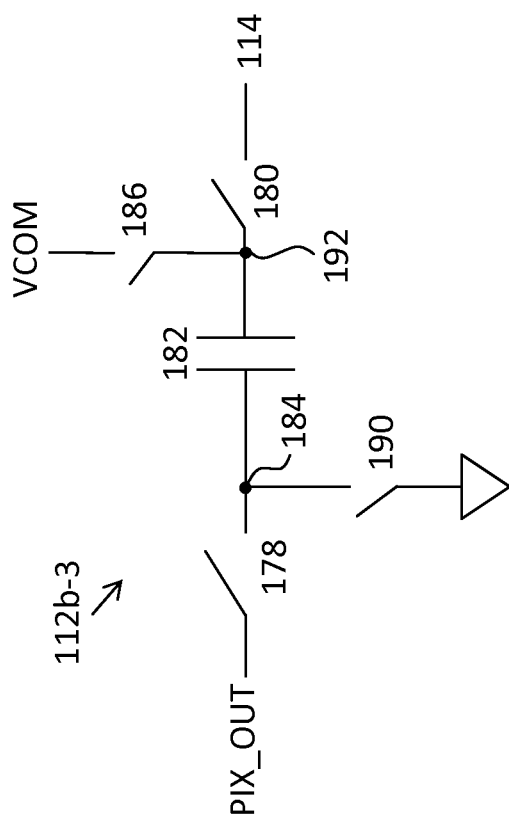


FIG. 3C

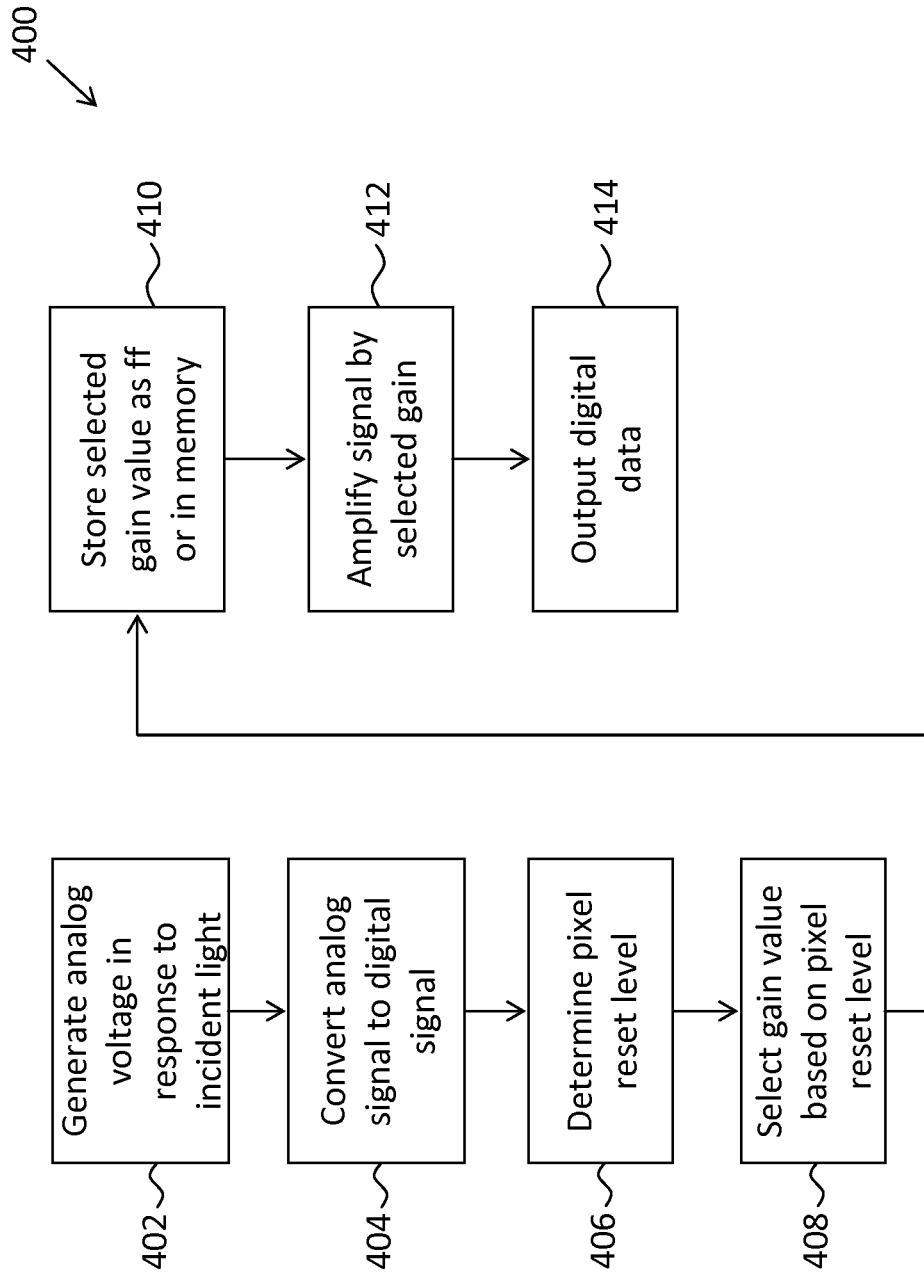


FIG. 4

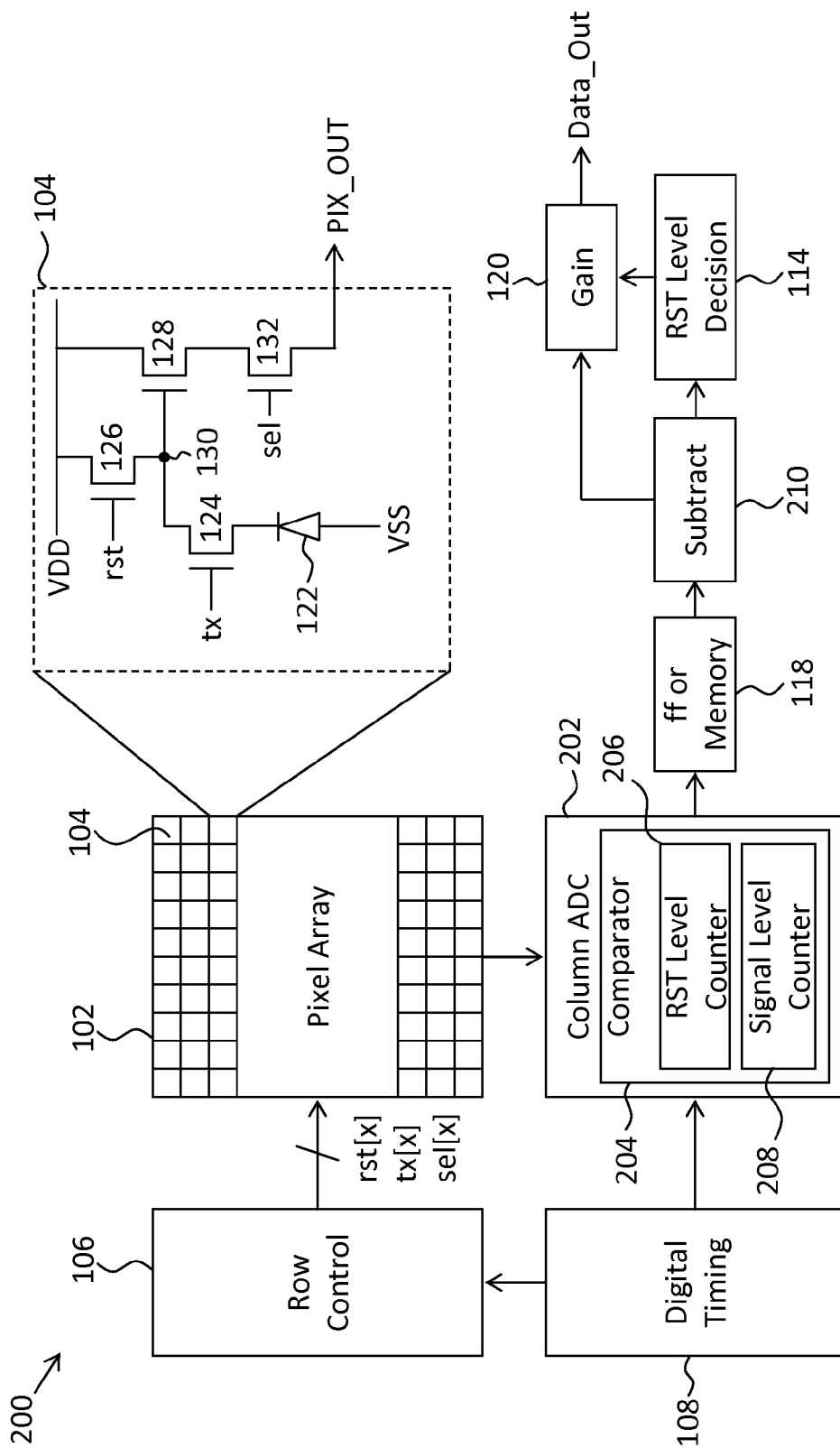


FIG. 5

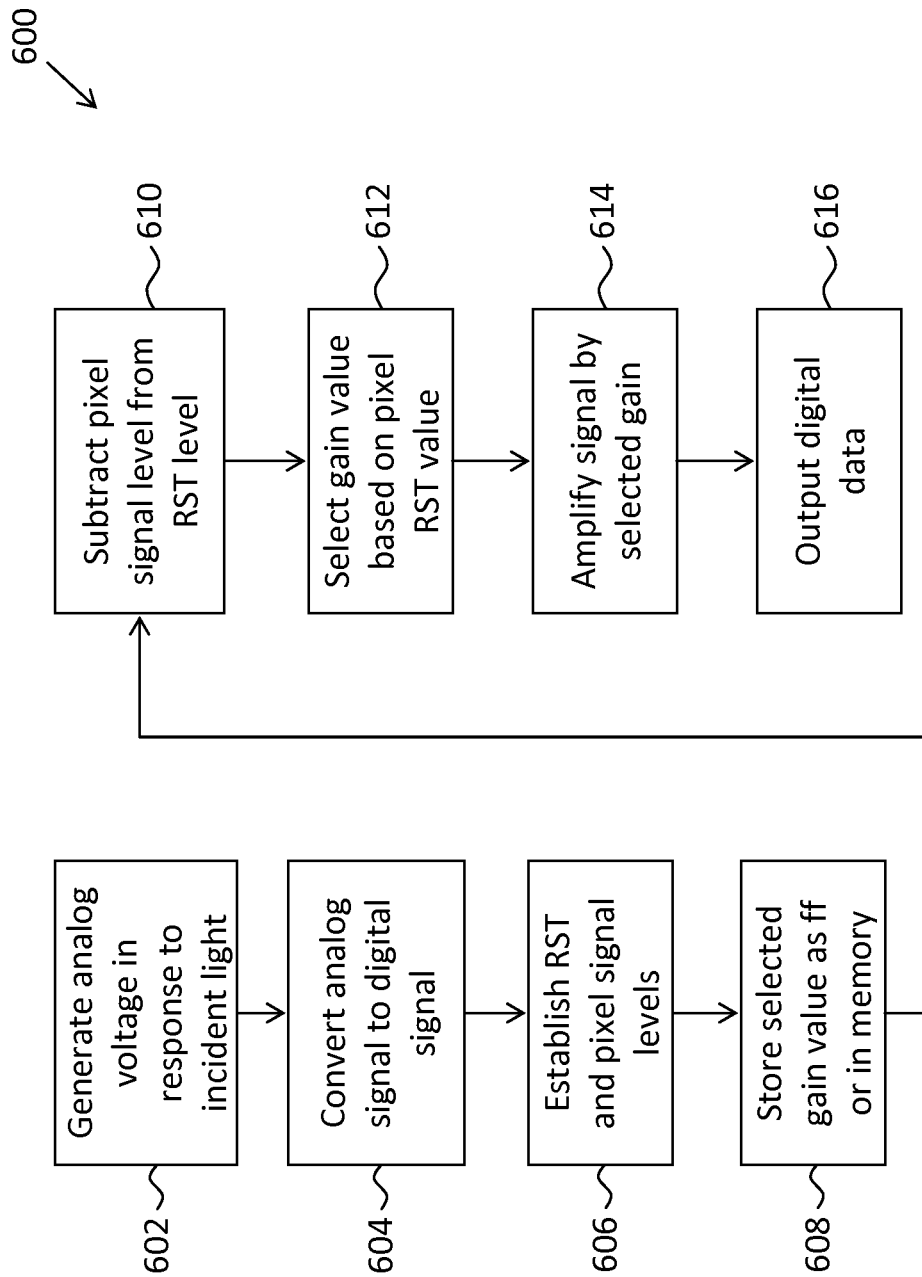


FIG. 6

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METHOD AND SYSTEMS FOR AMPLIFYING AN OUTPUT OF A CMOS PIXEL ARRAY

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is a continuation of U.S. patent application Ser. No. 13/410,785, filed Mar. 2, 2012, the entirety of which is incorporated by reference herein.

FIELD OF DISCLOSURE

The disclosed system and method relate to integrated circuits. More specifically, the disclosed system and method relate to integrated circuits for image sensors.

BACKGROUND

Complementary metal oxide semiconductor (CMOS) image sensors convert images to electrical signals. Such sensors are found in digital cameras or other electronic devices used for imaging. CMOS image sensors typically use source-followers as isolation devices. In particular, source followers are used to drive analog signals from individual pixel cells to a shared column line. However, the source followers in a pixel array do not all have the same gains, which results in an unbalanced photo response of the CMOS image sensor.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a block diagram of one example of an improved CMOS sensor array.

FIG. 2 is a circuit diagram of one example of a CDS and reset level extraction circuit in accordance with the CMOS sensor array illustrated in FIG. 1.

FIGS. 3A-3C illustrate various embodiments of reset level extraction circuits in accordance with the CDS and reset level extraction circuit illustrated in FIG. 2.

FIG. 4 is a flow diagram of one example of an improved sensing method with gain correction in accordance with the CMOS sensor array illustrated in FIG. 1.

FIG. 5 is a block diagram of another example of an improved CMOS sensor array.

FIG. 6 is a flow diagram of another example of an improved sensing method with gain correction in accordance with the CMOS sensor array illustrated in FIG. 5.

DETAILED DESCRIPTION

This description of the exemplary embodiments is intended to be read in connection with the accompanying drawings, which are to be considered part of the entire written description.

Some embodiments of the improved CMOS sensor arrays described herein advantageously determine a pixel reset voltage level of a CMOS pixel and adjust a gain of the output data based on the pixel reset voltage level. In some embodiments, adjusting a gain based on a detected pixel reset voltage level reduces the source follower gain variations across the array thereby reducing fixed pattern noise ("FPN") and minimizing photo response non-uniformities ("PRNU").

FIG. 1 illustrates one example of an improved CMOS imaging device 100 comprising an array 102 of CMOS pixels 104. A row control circuit 106 provides control signals, such as a reset signal, rst[x], tx[x], and a row selection signal, sel[x], to pixel array 102 for controlling the reading out of data from array 102. Array 102 is coupled to a row control

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circuit 106, which receives timing signals from digital timing circuit 108. Timing circuit 108 also provides timing signals to shift register 110 and to a correlated double sampling ("CDS") and reset level ("RST") extraction circuit 112, which determines the DC input level to the source-follower transistor 128.

CDS and RST level extraction circuit 112 is configured to receive pixel output signals, PIX_OUT, from pixel array 102 and output signals to a reset level decision circuit 114 and to programmable gain amplifier ("PGA") and analog to digital converter ("ADC") circuit 116. Reset level decision circuit 114 outputs the RST level to a flip-flop ("ff") or a memory 118. Both the PGA and ADC circuit 116 and the ff or memory 118 output signals to a gain circuit 120, which outputs a data output signal, Data_Out.

As shown in the inset of FIG. 1, pixel 104 includes a photodiode 122 configured to output an analog signal in response to receiving incident light. Diode 122 is coupled to a transistor 124, which is illustrated as an NMOS transistor, having its gate coupled to receive the tx signal from row control circuit 106. Transistor 124 is coupled to transistors 126 and 128 at node 130. Transistor 126 has its source coupled to a high voltage power supply, which may be VDD, its gate coupled to receive a reset signal, rst, from row control circuit 106, and its drain coupled to node 130. Source follower transistor 128 has its drain coupled to the high voltage power supply, its gate or input coupled to node 130, and its source coupled to transistor 132. Transistor 132 has its gate coupled to receive selection signal, sel, from row control circuit 106 such that transistor 132 selectively outputs the output signal, PIX_OUT. The output signal, PIX_OUT, is provided to CDS and RST level extraction circuit 112.

FIG. 2 illustrates one example of CDS and RST level extraction circuit 112. As shown in FIG. 2, CDS and RST extraction circuit 112 includes a CDS portion 112a and an RST extraction portion 112b that both receive the PIX_OUT signal from array 102. CDS portion 112a includes a pair of parallel switches 138 and 140, which receive the PIX_OUT signal and are respectively coupled to capacitors 142 and 144. Switch 146 is coupled to node 148, which is disposed between switch 138 and capacitor 142, and to node 150, which is disposed between switch 140 and capacitor 144. Capacitor 142 is coupled to switch 152, which is also coupled to an input of a differential amplifier 154. Capacitor 144 is coupled to switch 156, which is coupled to a second input of amplifier 154. Amplifier 154 is coupled to output a signal to PGA and ADC circuit 116 in which the noise. The signal output from amplifier 154 has a voltage equal to a difference between a pixel reset level and a pixel signal level.

RST extraction portion 112b includes a pair of parallel switches 158 and 160. Switch 158 is coupled to receive the PIX_OUT signal from array 102 and is coupled to switch 162 and capacitor 164 at node 166. Switch 160 is coupled to receive a reference voltage, VREF, which may be set at ground potential, VSS, or an arbitrary DC voltage. Switch 160 is also coupled to switch 162 and capacitor 168 at node 170. Capacitor 164 is coupled to switch 172, which selectively couples capacitor 164 to differential amplifier 174. Capacitor 168 is coupled to switch 176, which selective couples capacitor 168 to amplifier 174. Amplifier 174 outputs one or more signals that identify a difference between the pixel reset level and the reference voltage level to reset level decision circuit 114.

One skilled in the art will understand that RST extraction portion 112b may be implemented in other ways. For example, FIG. 3A illustrates another embodiment of an RST extraction circuit 112b-1 comprising a switches 178 and 180

and a comparator **182**, which are all coupled together at node **184**. Switch **178** is configured selectively provide the PIX_OUT signal received from array **102** to node **184**. Node **184** is selectively coupled to RST level decision circuit **114** through switch **180**.

FIG. 3B illustrates another example of an RST extraction circuit **112b-2**. As shown in FIG. 3B, the RST extraction circuit includes switches **178**, **180**, and **186**, a buffer **188**, and a capacitor **182**. Switch **178** selectively provides the PIX_OUT signal received from array **102** to node **184**, which is coupled to capacitor **182**, an input of buffer **188**, and to switch **186**. Switch **186** is configured to selectively provide a common voltage, VCOM, to node **184**. The output of buffer **188** is selectively provided to RST level decision circuit **114** through switch **180**.

FIG. 3C illustrates yet another embodiment of an RST extraction circuit **112b-3** that may be used in accordance with CDS and RST level extraction circuit **112** illustrated in FIG. 2. RST extraction circuit **112b-3** includes switches **178**, **180**, **186**, and **190** and a capacitor **182**. Switch **178** selectively provides the PIX_OUT signal received from array **102** to node **184**, which is coupled to capacitor **182** and to switch **190**. Node **190** selectively provides a low voltage power supply voltage, such as ground, to node **184**. Capacitor **182** is coupled to node **192**, which is coupled to switches **180** and **186**. Switch **186** selectively provides node **192** with a common voltage, VCOM, and switch **180** selectively provides the voltage at node **192** to RST level decision circuit **114**.

RST level decision circuit **114** is configured to receive the RST level from RST level extraction circuit **112b** and determines the appropriate gain based on the received signal level. For example, RST level decision circuit **114** may be configured to compare the RST level signal to one or more predetermined voltage levels that are identify the processing corner of the source-follower transistor **128**. In some embodiments, a first voltage threshold identifies a boundary between a slow-slow ("SS") corner and a typical-typical ("TT") corner of the source-follower transistor **128**, and a second voltage threshold identified a boundary between the TT corner and the fast-fast ("FF") corner of the source-follower transistor **128**.

The RST level decision circuit **114** may be configured to store a gain value in a memory, such as a flash memory, a random access memory ("RAM"), or other memory based on the level of the RST level signal to compensate for signal latency due to analog to digital conversion. For example, if the RST voltage level identifies that the source-follower transistor **128** operates in the SS corner, then RST level decision circuit **114** may store a value in memory that corresponds to a high-gain value, and if the RST voltage level identifies that the source-follower transistor **128** operates in the FF corner, then RST level decision circuit **114** may store a value in memory that corresponds to a low-gain value. If the RST voltage level identifies that the source-follower transistor **128** operates in the TT corner, then the RST level decision circuit **114** may store a value in memory that corresponds to a gain value that is between the high-gain value and the low-gain value. One skilled in the art will understand that RST level decision circuit **114** may be implemented as a state machine or using one or more comparators.

The operation of CMOS sensor array **100** is described with reference to FIG. 4, which is a flow diagram of one example of a sensing method **400** with gain correction. At block **402**, an analog signal, PIX_OUT, is output from a pixel **104** of array **102** in response to receiving incident light at photodiode **122**. As will be understood by one skilled in the art, the voltage at node **130** may initially be precharged to the voltage level of supply voltage VDD. When incident light is received

at photo diode **122**, the voltage at node **130** drops due to charge flow within photodiode **122** producing a voltage at node **130** that is lower than supply voltage VDD.

At block **404**, the analog signal from array **102** is sampled by CDS and RST level extraction circuit **112**. CDS portion **112a** of CDS and RST level extraction circuit **112** samples the PIX_OUT signal and outputs an analog signal to PGA and ADC circuit **116** having a voltage equal to the difference between the RST level, which may be stored on capacitor **142**, and the pixel signal level, which may be stored on capacitor **144**. As will be understood by one skilled in the art, switches **138** and **140** alternately switch such that capacitor **144** is charged with the RST level and capacitor **144** is charged with the pixel signal level having a voltage less than the RST level. RST level extraction portion **112b** samples the PIX_OUT signal and a reference signal, VREF, and outputs a sampled analog signal to RST level decision circuit **114**. The sampled signal output from RST level extraction portion **112b** has a value equal to the pixel RST level as the reference voltage, VREF, may be set at ground potential, VSS, or a random DC voltage.

At block **406**, a determination concerning the pixel RST level is made. In some embodiments, the determination concerning the pixel RST level is made by comparing the pixel RST level to one or more threshold voltages. As described above, for example, the threshold voltages may identify boundaries between the SS and TT process corners and the TT and FF process corners source-follower transistor **128** of a pixel **104**. In some embodiments, blocks **404** and **406** are performed simultaneously.

At block **408**, a gain value is selected based on the pixel RST level. For example, if the pixel RST level, which is based on the gain of the source-follower transistor **128**, identifies that the source-follower transistor **128** of a pixel **104** is operating in the SS corner, then RST level decision circuit **114** select a high-gain value, and if the RST voltage level identifies that the source-follower transistor **128** of the pixel **104** is operating in the FF corner, then RST level decision circuit **114** may select a low-gain value. If the RST voltage level identifies that the source-follower transistor **128** of the pixel **104** is operating in the TT corner, then the RST level decision circuit **114** may select a gain value that is between the high-gain value and the low-gain value.

At block **410**, the selected gain level, or a digital signal identifying the selected gain value, is stored in a flip flop or in a memory. The selected gain value is stored in a flip flop or in a memory to compensate for any latency between the signals processed by RST level decision circuit **114** and the analog to digital conversion of the PGA/ADC circuit **116**.

At block **412**, the digital signal output from PGA/ADC circuit **116** is amplified at gain block **120**. The gain by which the digital signal is amplified is the gain value selected by RST level decision block **114** and delayed by the flip flop or by the retrieval of the value from memory. Gain circuit **120** outputs the digital data signal, Data_Out, at block **414**.

FIG. 5 illustrates another embodiment of an improved CMOS imaging device **200**. CMOS imaging device **200** includes an array **102** of CMOS pixels **104**, a row control circuit **106** for providing control signals to array **102**, and a digital timing circuit **108**. A column analog to digital converter ("ADC") **202** is coupled to array **102** and to digital timing circuit **108**. Column ADC **202** is configured to perform analog to digital conversion for each column of pixels **104** of array **102**.

Column ADC **202** also includes one or more comparators **204**, RST level counters **206**, and signal level counters **208**. As will be understood by one skilled in the art, a comparator

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204 in each column compares a ramp wave generated by a digital to analog converter (not shown) with the pixel output. RST level counters **206** and signal level counters **208** may be implemented as ripple counters configured to count the number of clock cycles between changes in the output of the column comparator **204**.

The output of column ADC **202** is coupled to a flip flop or memory **118**, which is configured to remove any latency due to analog to digital conversion of the voltage signal in each column. A subtraction circuit **210** is coupled to the output of the flip flop or memory **118** and is coupled to both a gain circuit **120** and a RST level decision circuit **114**. Subtraction circuit **210** is configured to subtract the pixel signal level from the RST level. RST level decision circuit **114** is configured to receive the difference between the RST level and the pixel signal level and determine a gain that should be applied by gain circuit **120**. The output of the gain circuit **120** is a Data_Out signal.

The operation of CMOS sensor array **200** is described with reference to FIG. 6, which is a flow diagram of one example of a sensing method **600** with gain correction. At block **602**, an analog signal, PIX_OUT, is output from a pixel **104** of array **102** in response to receiving incident light at photodiode **122**. As will be understood by one skilled in the art, the voltage at node **130** may initially be precharged to the voltage level of supply voltage VDD. When incident light is received at photo diode **122**, the voltage at node **130** drops due to charge flow within photodiode **122** producing a voltage at node **130** that is lower than supply voltage VDD. The analog signal output from pixel **104** is converted to a digital signal by column ADC **202** at block **604**.

At block **606**, the RST level and pixel signal levels are established. In some embodiments, the RST level is established by RST level counter **206** counting the number of clock signals between changes in the output of comparator **204** during a first time period (e.g., a RST signal A/D conversion period), and the pixel signal level is established by pixel level counter **208** by counting the number of clock cycles between changes in the output of comparator **204** during a second time period (e.g., a data A/D conversion period). The RST level value and pixel signal value may be stored in a flip flop or in a memory **118** at block **608**.

At block **610**, the pixel signal level is subtracted from the RST level at subtraction circuit **210**. The RST level is used by RST level decision circuit **114** to determine an appropriate gain at block **612**. In some embodiments, the pixel RST level is determined by comparing the pixel RST level to one or more threshold voltages. As described above, for example, the threshold voltages may identify boundaries between the SS and TT process corners and the TT and FF process corners source-follower transistor **128** of a pixel **104**.

For example, if the pixel reset level, e.g., RST voltage level, identifies that the source-follower transistor **128** of a pixel **104** is operating in the SS corner, then RST level decision circuit **114** select a high-gain value, and if the RST voltage level identifies that the source-follower transistor **128** of the pixel **104** is operating in the FF corner, then RST level decision circuit **114** may select a low-gain value. If the RST voltage level identifies that the source-follower transistor **128** of the pixel **104** is operating in the TT corner, then the RST level decision circuit **114** may select a gain value that is between the high-gain value and the low-gain value.

At block **614**, the digital signal output from the column ADC **202** is amplified at gain block **120**. The gain by which the digital signal is amplified is the gain value selected by RST level decision block **114** and delayed by the flip flop or

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by the retrieval of the value from memory. Gain circuit **120** outputs the digital data signal, Data_Out, at block **616**.

The improved CMOS sensor arrays described above advantageously determine a pixel reset voltage level of a CMOS pixel and adjust a gain of the output data based on the pixel reset voltage level. Adjusting a gain of a source followed based on a detected pixel reset voltage level reduces the source follower gain variations across the array thereby reducing FPN and minimizing PRNU.

In some embodiments, a CMOS sensor includes a pixel configured to output a voltage based on incident light received by the pixel. A first circuit is coupled to the pixel and is configured to determine a reset voltage of the pixel. A second circuit is coupled to the first circuit and is configured to select a gain level based on the reset voltage of the pixel. A gain circuit is coupled to the second circuit and is configured to set a voltage level of the gain selected by the second circuit.

In some embodiments, a method includes receiving an analog signal from a pixel of an image sensor, determining a reset level of the pixel, selecting a gain value based on the reset level of the pixel, and amplifying a digital data signal with the selected gain value.

In some embodiments, a CMOS sensor includes a pixel array including a plurality of pixels arranged in rows and columns. Each pixel is configured to output an analog signal in response to receiving incident light. A first circuit is coupled to at least one of the pixels of the pixel array. The first circuit is configured to determine a reset voltage of the at least one pixel. A second circuit is coupled to the first circuit and is configured to select a gain level based on the reset voltage of the pixel. A gain circuit is coupled to the second circuit and is configured to set a voltage level of the gain selected by the second circuit.

Although the invention has been described in terms of exemplary embodiments, it is not limited thereto. Rather, the appended claims should be construed broadly, to include other variants and embodiments of the invention, which may be made by those skilled in the art without departing from the scope and range of equivalents of the invention.

What is claimed is:

1. A CMOS sensor, comprising:

a pixel configured to output an analog signal in response to incident light received by the pixel;

circuitry coupled to the pixel and configured to determine a reset voltage of the pixel in response to receiving the analog signal from the pixel, the circuitry further being configured to select a gain level based on the reset voltage of the pixel; and

a gain circuit coupled to the circuitry and configured to amplify a digital data signal with the selected gain level.

2. The CMOS sensor of claim 1, wherein the circuitry includes:

a first circuit configured to determine the reset voltage of the pixel, and

a second circuit configured to select the gain level based on the reset voltage of the pixel as determined by the first circuit.

3. The CMOS sensor of claim 2, wherein the second circuit is configured to compare the reset voltage level to at least one threshold voltage to identify a process corner in which a source-follower transistor of the pixel is operating.

4. The CMOS sensor of claim 2, wherein the first circuit includes

a first portion configured to perform correlated double sampling of the voltage output from the pixel, and a

a second portion configured to determine the reset voltage of the pixel.

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5. The CMOS sensor of claim 4, wherein the second portion includes:

a differential amplifier having a first input coupled to a first capacitor through a first switch, a second input coupled to a second capacitor through a second switch, and an output coupled to the second circuit;

a third switch configured to selectively provide the voltage from the pixel to the first capacitor; and

a fourth switch configured to selectively provide a reference voltage to the second capacitor.

6. The CMOS sensor of claim 4, wherein the second portion includes a pair of switches configured to selectively provide the voltage from the pixel to a capacitor and to the second circuit.

7. The CMOS sensor of claim 6, wherein the capacitor is coupled to ground and to a node disposed between the pair of switches.

8. The CMOS sensor of claim 2, wherein the first circuit includes

an analog to digital converter configured to convert the voltage output by the pixel to a digital value;

a first counter configured to measure the reset voltage; and

a second counter configured to measure a signal voltage output by the pixel.

9. The CMOS sensor of claim 8, further comprising a subtraction circuit coupled to the first and second counters and configured to provide a difference between the signal voltage and the reset voltage to the second circuit.

10. A method, comprising:

determining a reset level of a pixel of an image sensor in response to receiving an analog signal from the pixel;

selecting a gain value based on the reset level of the pixel; and

amplifying a digital data signal with the selected gain value.

11. The method of claim 10, wherein determining the reset level of the pixel includes

sampling an output of the pixel of the image sensor during a reset period to provide a differential amplifier with a first input;

sampling a reference voltage to provide the differential amplifier with a second input; and

outputting the reset level of the pixel from the differential amplifier based on the first and second inputs.

12. The method of claim 10, wherein selecting the gain value includes comparing the reset level of the pixel to at least one threshold value.

13. The method of claim 10, further comprising:

converting the analog signal to a digital signal;

measuring a reset level of the pixel at a first digital counter during a first time period;

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measuring a signal level output by the pixel at a second digital counter during a second time period; subtracting the signal level from the reset level; and outputting the difference between the signal level and the reset level to a circuit for selecting the gain value.

14. A CMOS sensor, comprising:

a pixel array including a plurality of pixels arranged in rows and columns, each pixel configured to output an analog voltage signal in response to receiving incident light;

circuitry coupled to at least one of the pixels of the pixel array, the circuitry configured to determine a reset voltage of the at least one pixel and to select a gain level based on the reset voltage of the pixel; and

a gain circuit coupled to the circuitry and configured to set a voltage level of the gain selected by the circuitry.

15. The CMOS sensor of claim 14, wherein the circuitry is configured to compare the reset voltage level to at least one threshold voltage to identify a process corner in which a source-follower transistor of the pixel is operating.

16. The CMOS sensor of claim 14, wherein the circuitry includes:

a first portion configured to perform correlated double sampling of the voltage output from the pixel, and

a second portion configured to determine the reset voltage of the pixel.

17. The CMOS sensor of claim 16, wherein the second portion includes:

a differential amplifier having a first input coupled to a first capacitor through a first switch, a second input coupled to a second capacitor through a second switch, and an output coupled to the second circuit;

a third switch configured to selectively provide the voltage from the pixel to the first capacitor; and

a fourth switch configured to selectively provide a reference voltage to the second capacitor.

18. The CMOS sensor of claim 16, wherein the second portion includes a pair of switches configured to selectively provide the voltage from the pixel to a capacitor and to the second circuit.

19. The CMOS sensor of claim 14, wherein the circuitry includes:

an analog to digital converter configured to convert the voltage output by the at least one pixel to a digital value;

a first counter configured to measure the reset voltage; and

a second counter configured to measure a signal voltage output by the pixel.

20. The CMOS sensor of claim 19, further comprising a subtraction circuit coupled to the first and second counters and configured to provide a difference between the signal voltage and the reset voltage to the circuitry.

* * * * *

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION


PATENT NO. : 9,402,043 B2
APPLICATION NO. : 14/250411
DATED : July 26, 2016
INVENTOR(S) : Kuo-Yu Chou et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the Title page, item (54) and in the Specification, column 1 Title:
Delete "SYSTEMS" and insert -- SYSTEM --

Signed and Sealed this
Fourth Day of October, 2016

A handwritten signature in black ink, reading "Michelle K. Lee". The signature is fluid and cursive, with the first letters of each name being capitalized and prominent.

Michelle K. Lee
Director of the United States Patent and Trademark Office